

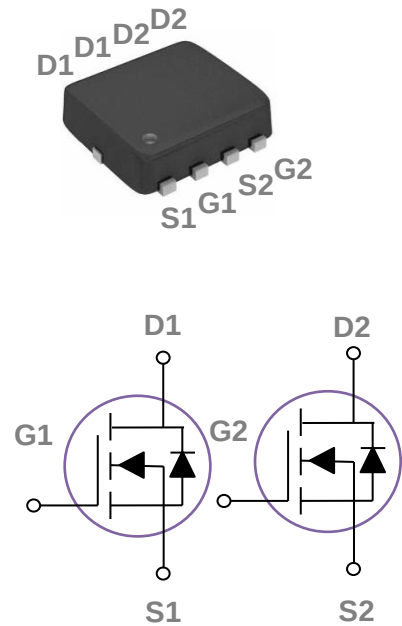
Description:

This Dual N-Channel MOSFET uses advanced SGT technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=60V, I_D=22A, R_{DS(on)} < 20m\Omega @ V_{GS}=10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(on)}$.
- 5) Excellent package for good heat dissipation.



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
DOZ20DN06T	20DN06T	DFN3*3-8D	5000 pcs/Reel

Absolute Maximum Ratings: ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current	22	A
	Continuous Drain Current- $T_c=100^\circ\text{C}$	13.2	
I_{DM}	Pulsed Drain Current ¹	88	
P_D	Power Dissipation	16.5	W
E_{AS}	Single pulse avalanche energy ²	25	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	7.5	$^\circ\text{C}/\text{W}$

Electrical Characteristics: ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Sourtce Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	60	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =60V	---	---	1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	GATE-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	1	1.5	2.2	V
R _{DS(ON)}	Drain-Source On Resistance ³	V _{GS} =10V, I _D =20A	---	15.6	20	m Ω
		V _{GS} =4.5V, I _D =10A	---	20	26	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1MHz	---	470	---	pF
C _{oss}	Output Capacitance		---	195	--	
C _{rss}	Reverse Transfer Capacitance		---	6.5	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DS} =30V, I _D =20A, R _G =6 Ω ,V _{GS} =10V	---	3.2	---	ns
t _r	Rise Time		---	3.9	---	ns
t _{d(off)}	Turn-Off Delay Time		---	12	---	ns
t _f	Fall Time		---	5.6	---	ns
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =30V, I _D =20A	---	12.3	---	nc
Q _{gs}	Gate-Source Charge		---	1.2	---	nc
Q _{gd}	Gate-Drain “Miller” Charge		---	2.6	---	nc
Drain-Source Diode Characteristics						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _{SD} =20A	---	---	1.2	V
I _S	Continuous Drain Curren	VD=VG=0V	---	---	22	A
I _{SM}	Pulsed Drain Current		---	---	88	A
T _{rr}	Reverse Recovery Time	I _F =15A, T _J =25 °C	---	20	---	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/us	---	8.1	---	nc

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting $T_J=25^\circ\text{C}$, $V_{DD}=30\text{V}$, $V_G=10\text{V}$, $R_G=25\Omega$, $L=0.5\text{mH}$, $I_{AS}=10\text{A}$
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Typical Characteristics: ($T_c=25^\circ\text{C}$ unless otherwise noted)

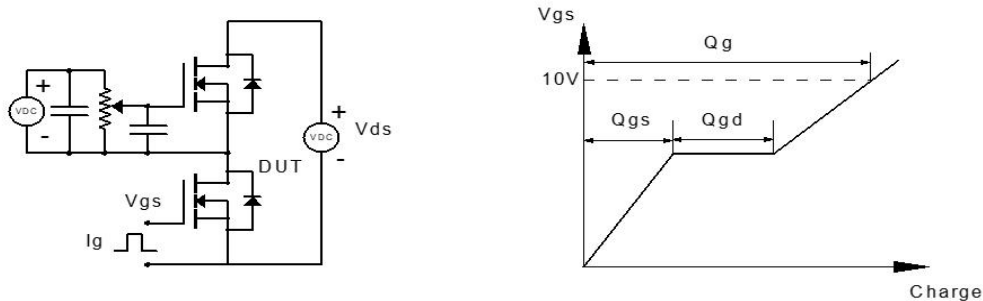


Figure 1: Gate Charge Test Circuit & Waveform

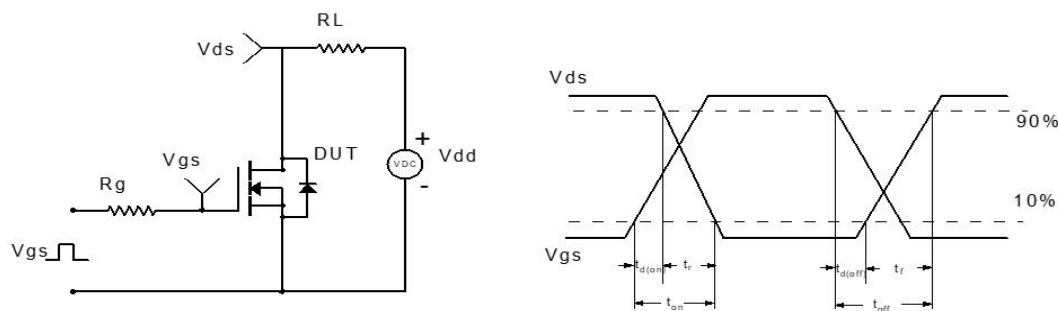


Figure 2: Resistive Switching Test Circuit & Waveform

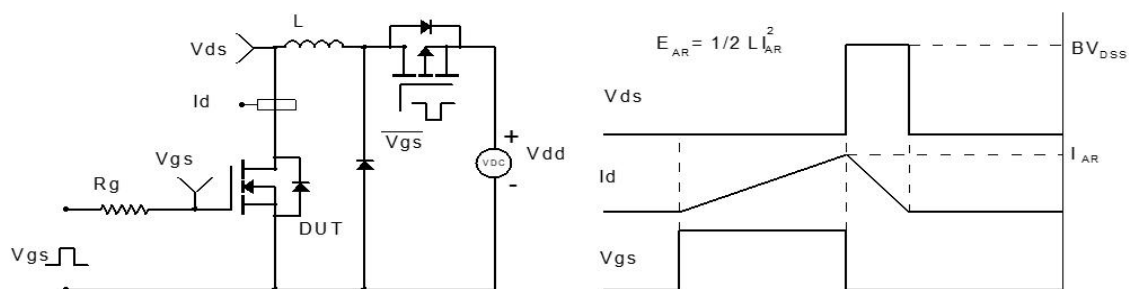


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

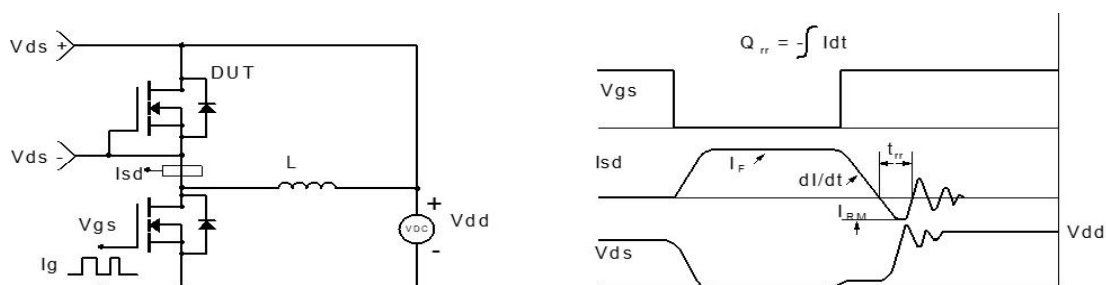
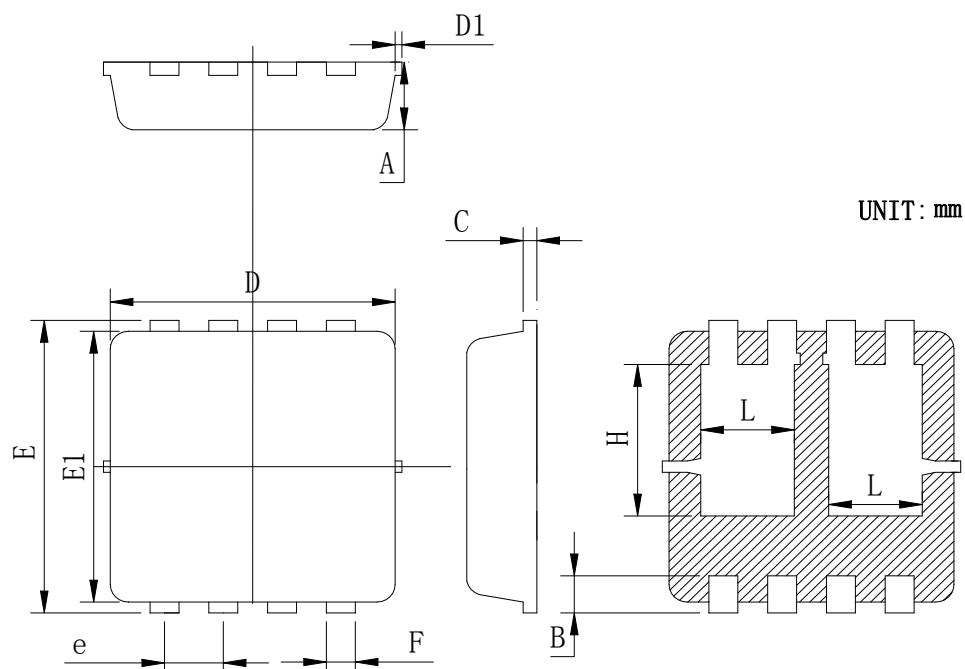
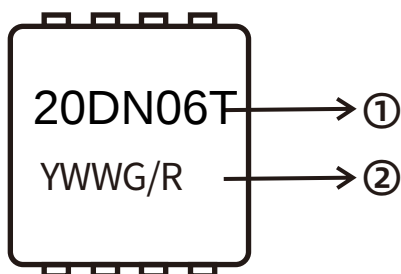


Figure 4: Diode Recovery Test Circuit & Waveform

DFN3X3-8D Package Outline Data


Symbol	Min	Typ	Max
A	0.725	0.775	0.825
B	0.28	0.38	0.48
C	0.13	0.15	0.20
D	3.05	3.15	3.25
D1			0.10
E	3.25	3.35	3.45
E1	3.0	3.1	3.2
e	0.60	0.65	0.70
F	0.27	0.32	0.37
H	1.63	1.73	1.83
L	0.93	1.03	1.13

Marking Information:



①: Part NO.

②: Date Code (YWWG / R)

Y: Year Code , last digit of the year

WW : Week Code (01-53)

G/R: G(Green) /R(Lead Free)

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